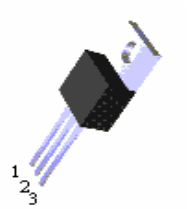
FEATURE/APPLICATIONS

- Case TO-220
- Planar Structure
- V_{DRM} 400V
  500V
  600V
- $I_{T(RMS)}$ 8A
- I_{TRM} 50A
- Solid State Relays
- Light-control Equipment
- Heater-control Equipment
- Motor-control Equipment

TO-220



Pin: 1.A1
2.A2
3.G

ORDERING INFORMATION

Device	Operating Temperature	Package
PJT8A60CZ	-20℃ ~ +85•C	TO-220

ABSOLUTE MAXIMUM RATINGS(Ta=25 ℃)

Parameters	Symbol	Ratings			Units
		PJT440	PJT450	PJT460	
Non repetitive peak off-state voltage	V_{DRM}	500	600	700	V
Repetitive peak off-state voltage	V_{DRM}	400	500	600	V
RMS on-state current	$I_{T(DRM)}$	8 (Tc = 107•C)			A
Surge non repetitive on-state current	V_{TSM}	80 (50Hz 1cycle) 88 (60Hz 1cycle)			A
I^2t Value	A^2S	28 (1ms to 10ms)			A^2S
Critical rate of rise of on-state current	$D1_T/dt$	50			A/μs
Peak gate power dissipation	P_{GM}	5 (f 50Hz, Duty 10%)			W
Average gate power dissipation	$P_{O(AV)}$	0.5			W
Peak gate current	I_{CM}	±3 (f 50Hz, Duty 10%)			A
Junction temperature	T_J	-40~+125			℃
Storage temperature	Tstg	-55~+150			℃
Weight	-	2			g

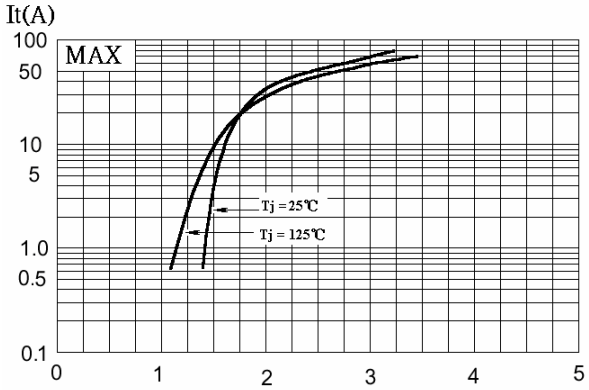


Fig. 1: On-state voltage Vt(V)

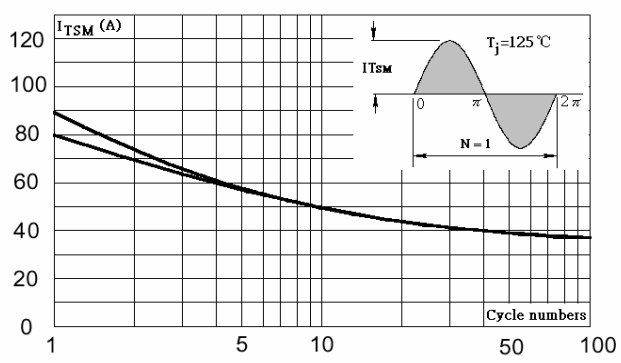


Fig. 2: Peak surge current Vs on cycles

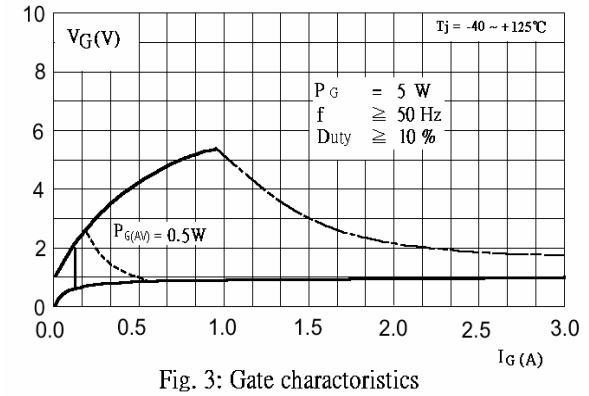


Fig. 3: Gate charactoristics

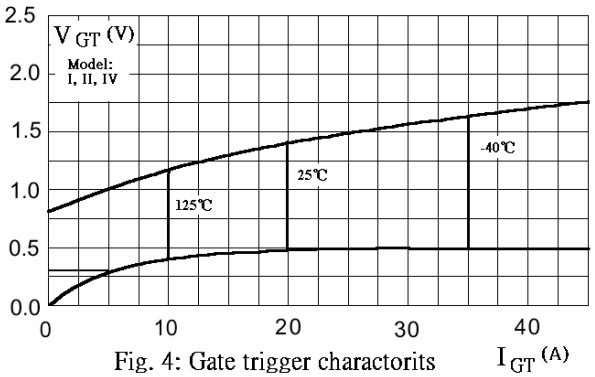


Fig. 4: Gate trigger charactorits

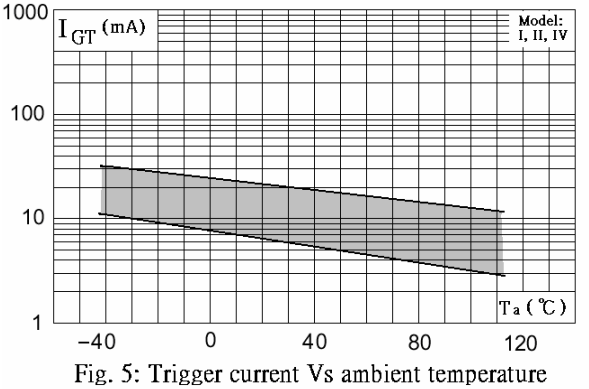


Fig. 5: Trigger current Vs ambient temperature

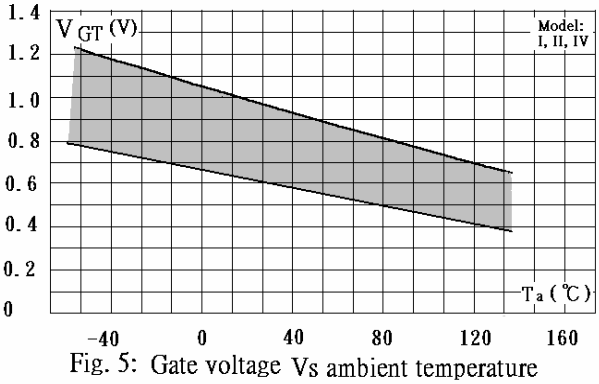


Fig. 5: Gate voltage Vs ambient temperature

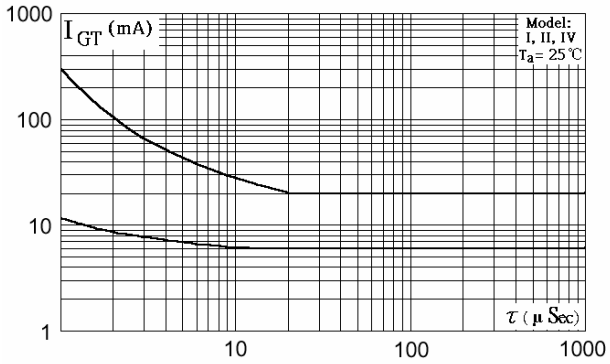


Fig.7 : Gate trigger current Vs pulse width

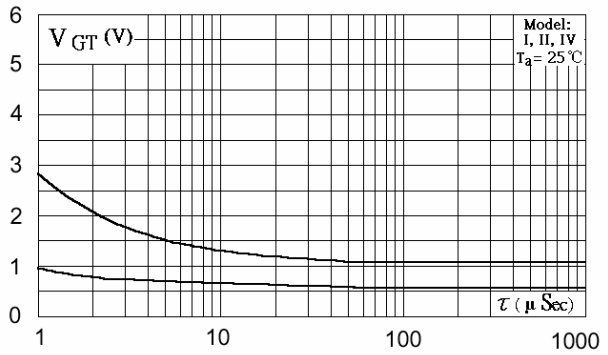


Fig. 8: Gate trigger voltage Vs pulse width

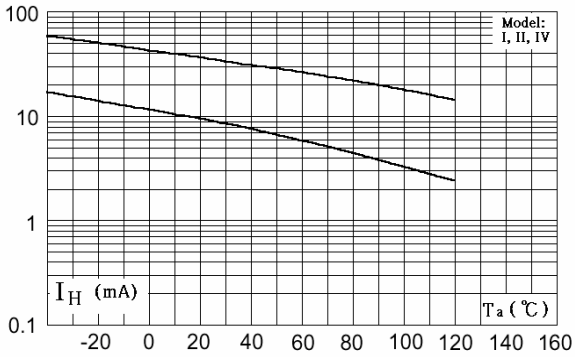


Fig. 9: Holding current Vs ambient temperature

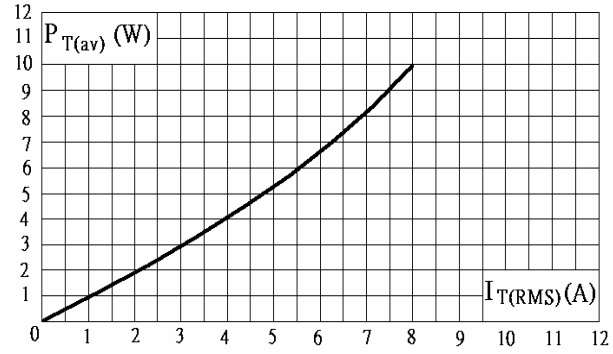


Fig.10: Power disipation(avg) Vs On-state current (rms)

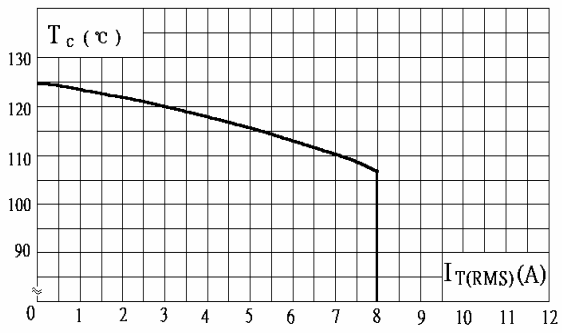
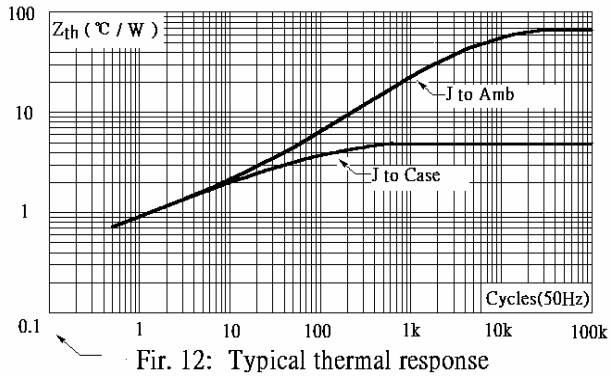


Fig.11: Case temperature Vs On-state current (rms)



Fir. 12: Typical thermal response

TO-220 Unit:mm